

NTP4302, NTB4302

Power MOSFET 74 Amps, 30 Volts N-Channel TO-220 and D²PAK

Features

- Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Diode Exhibits High Speed, Soft Recovery
- Avalanche Energy Specified
- I_{DSS} Specified at Elevated Temperature

Typical Applications

- DC-DC Converters
- Low Voltage Motor Control
- Power Management in Portable and Battery Powered Products: I.e: Computers, Printers, Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	30	Vdc
Drain-to-Gate Voltage ($R_{GS} = 10\text{ M}\Omega$)	V_{DGR}	30	Vdc
Gate-to-Source Voltage - Continuous	V_{GS}	± 20	Vdc
Drain Current			
- Continuous @ $T_C = 25^\circ\text{C}$	I_D	74	Adc
- Continuous @ $T_C = 100^\circ\text{C}$	I_D	47	
- Single Pulse ($t_p \leq 10\text{ }\mu\text{s}$)	I_{DM}	175	Apk
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	80 0.66	W W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to $+150$	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy - Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 30\text{ Vdc}$, $V_{GS} = 10\text{ Vdc}$, $L = 5.0\text{ mH}$ $I_{L(pk)} = 17\text{ A}$, $V_{DS} = 30\text{ Vdc}$, $R_G = 25\text{ }\Omega$)	E_{AS}	722	mJ
Thermal Resistance			$^\circ\text{C/W}$
- Junction-to-Case	$R_{\theta JC}$	1.55	
- Junction-to-Ambient (Note 1)	$R_{\theta JA}$	70	
Maximum Lead Temperature for Soldering Purposes, $1/8"$ from case for 10 seconds	T_L	260	$^\circ\text{C}$

1. When surface mounted to an FR4 Board using minimum recommended Pad Size, (Cu Area 0.412 in^2).
2. Current limited by internal lead wires.

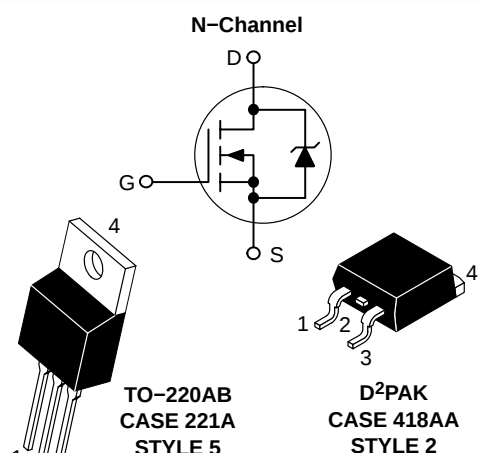


ON Semiconductor®

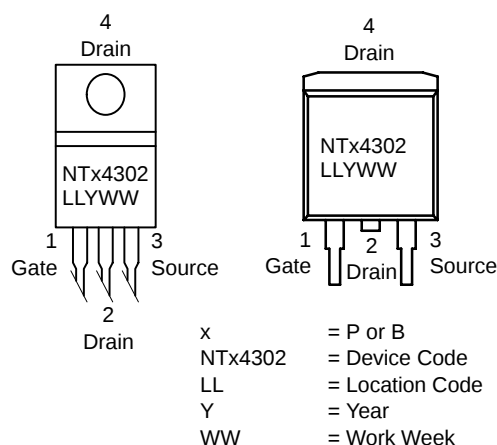
<http://onsemi.com>

**74 AMPERES
30 VOLTS**

$R_{DS(on)} = 9.3\text{ m}\Omega$ Max



MARKING DIAGRAMS & PIN ASSIGNMENTS



ORDERING INFORMATION

Device	Package	Shipping
NTP4302	TO-220AB	50 Units/Rail
NTB4302	D ² PAK	50 Units/Rail
NTB4302T4	D ² PAK	800/Tape & Reel

NTP4302, NTB4302

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 3) ($V_{GS} = 0\text{ Vdc}$, $I_D = 250\text{ }\mu\text{Adc}$) Temperature Coefficient (Positive)	$V_{(BR)DSS}$	30 –	– 25	– –	Vdc mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current ($V_{DS} = 30\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 30\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	I_{DSS}	– –	– –	1.0 10	μAdc
Gate-Body Leakage Current ($V_{GS} = \pm 20\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	–	–	± 100	nAdc

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (Note 3) ($V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{Adc}$) Threshold Temperature Coefficient (Negative)	$V_{GS(th)}$	1.0 –	1.9 –3.8	3.0 –	Vdc mV/ $^\circ\text{C}$
Static Drain-to-Source On-Resistance (Note 3) ($V_{GS} = 10\text{ Vdc}$, $I_D = 37\text{ Adc}$) ($V_{GS} = 10\text{ Vdc}$, $I_D = 20\text{ Adc}$) ($V_{GS} = 4.5\text{ Vdc}$, $I_D = 10\text{ Adc}$)	$R_{DS(on)}$	–	6.8 6.8 9.5	9.3 9.3 12.5	m Ω
Forward Transconductance (Note 3) ($V_{DS} = 10\text{ Vdc}$, $I_D = 20\text{ Adc}$)	g_{FS}	–	40	–	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = 24\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{iss}	–	2050	2400	pF
Output Capacitance		C_{oss}	–	640	800	
Transfer Capacitance		C_{rss}	–	225	310	

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$(V_{DD} = 24\text{ Vdc}$, $I_D = 20\text{ Adc}$, $V_{GS} = 10\text{ Vdc}$, $R_G = 2.5\text{ }\Omega$) (Note 3)	$t_{d(on)}$	–	10	18	ns
Rise Time		t_r	–	22	35	
Turn-Off Delay Time		$t_{d(off)}$	–	45	75	
Fall Time		t_f	–	35	70	
Turn-On Delay Time	$(V_{DD} = 24\text{ Vdc}$, $I_D = 10\text{ Adc}$, $V_{GS} = 4.5\text{ Vdc}$, $R_G = 2.5\text{ }\Omega$) (Note 3)	$t_{d(on)}$	–	18	–	ns
Rise Time		t_r	–	70	–	
Turn-Off Delay Time		$t_{d(off)}$	–	32	–	
Fall Time		t_f	–	30	–	
Gate Charge	$(V_{DS} = 24\text{ Vdc}$, $I_D = 37\text{ Adc}$, $V_{GS} = 4.5\text{ Vdc}$) (Note 3)	Q_T	–	28	–	nC
		Q_{gs}	–	7.5	–	
		Q_{gd}	–	19	–	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	$(I_S = 20\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$) (Note 3) $(I_S = 20\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	V_{SD}	– –	0.90 0.75	1.3 –	Vdc
Reverse Recovery Time	$(I_S = 20\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$, $di_S/dt = 100\text{ A}/\mu\text{s}$) (Note 3)	t_{rr}	–	37	–	ns
		t_a	–	21	–	
		t_b	–	16	–	
Reverse Recovery Stored Charge		Q_{RR}	–	0.035	–	μC

- Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

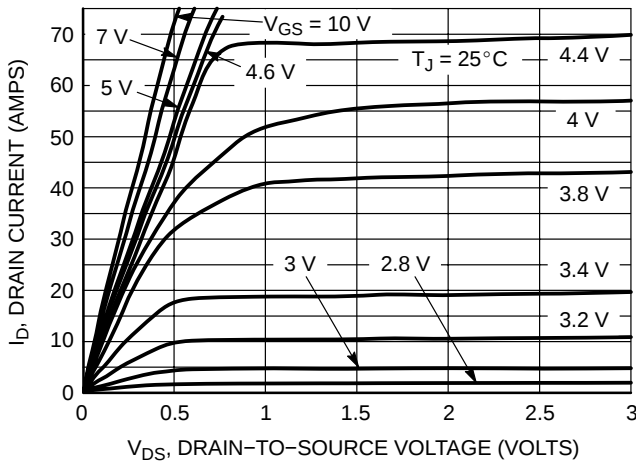


Figure 1. On-Region Characteristics

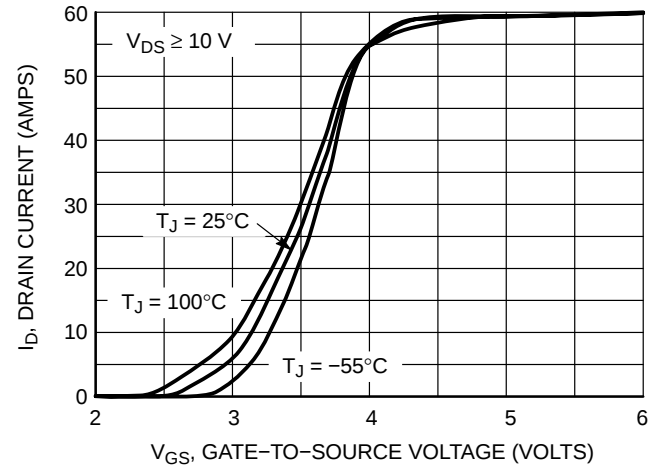


Figure 2. Transfer Characteristics

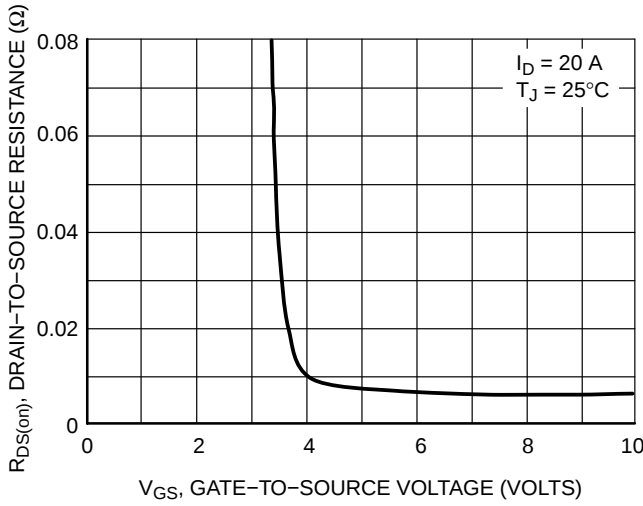


Figure 3. On-Resistance versus Gate-to-Source Voltage

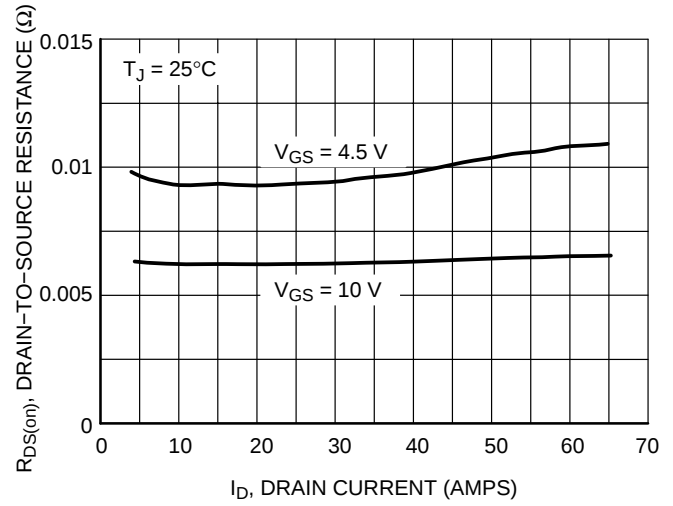


Figure 4. On-Resistance versus Drain Current and Gate Voltage

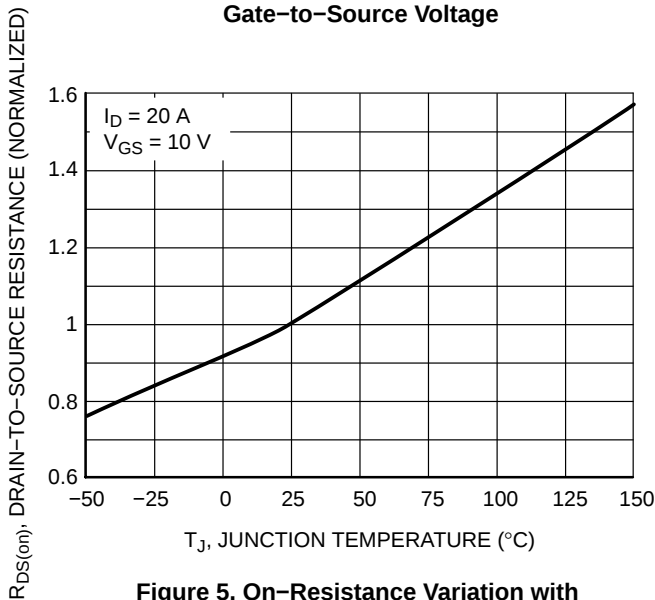


Figure 5. On-Resistance Variation with Temperature

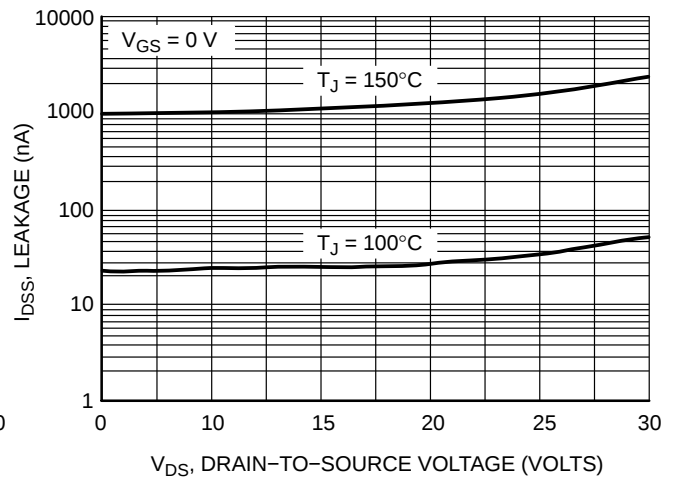


Figure 6. Drain-to-Source Leakage Current versus Voltage

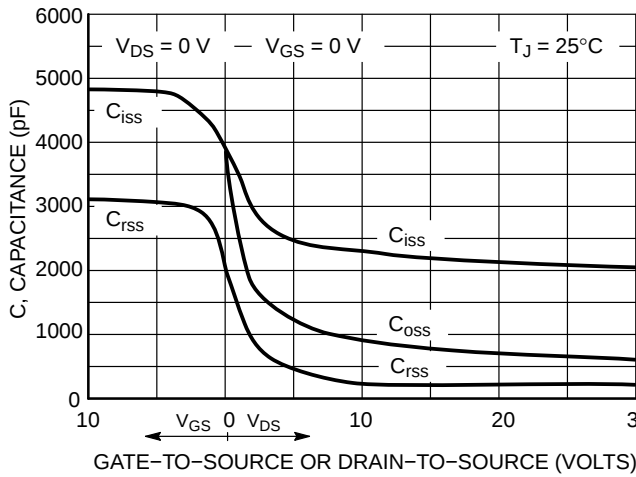


Figure 7. Capacitance Variation

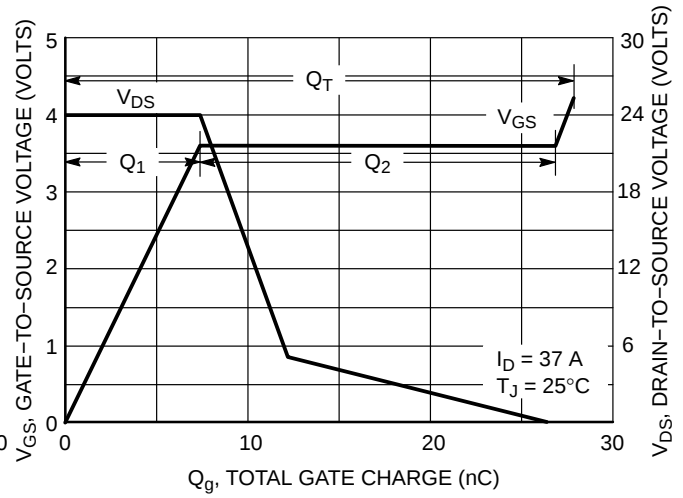


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

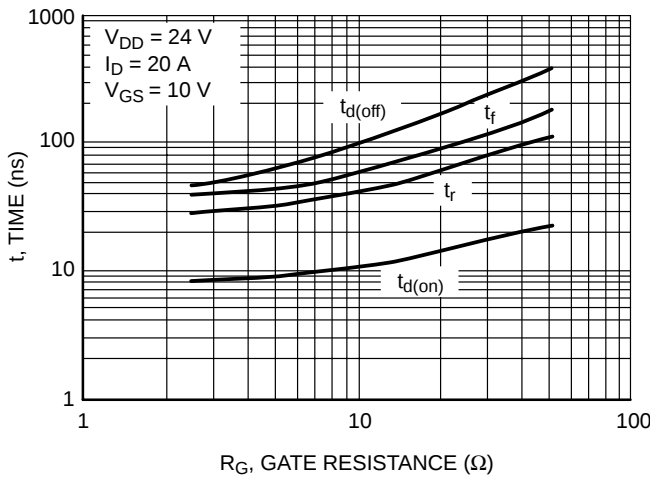


Figure 9. Resistive Switching Time Variations versus Gate Resistance

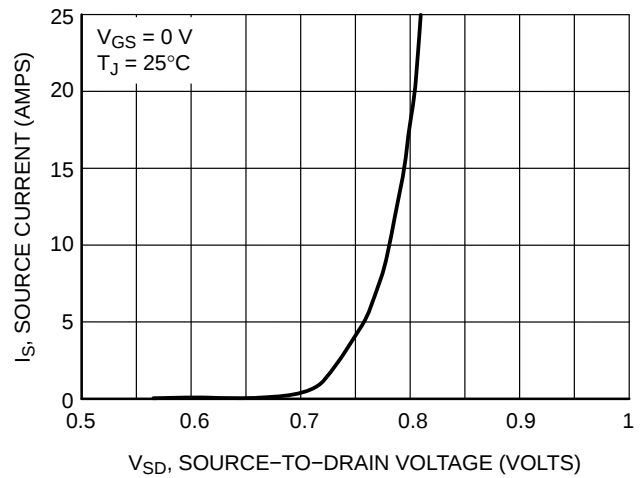


Figure 10. Diode Forward Voltage versus Current

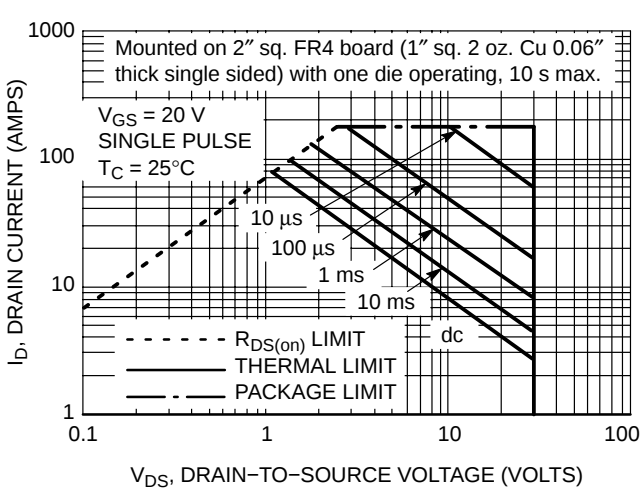


Figure 11. Maximum Rated Forward Biased Safe Operating Area

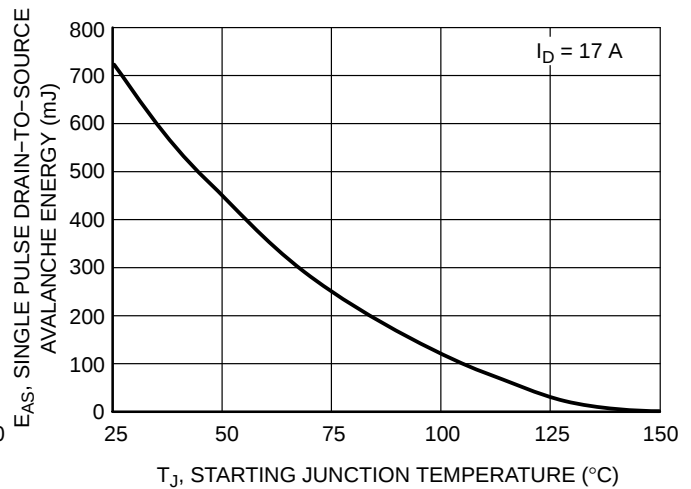


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

SAFE OPERATING AREA

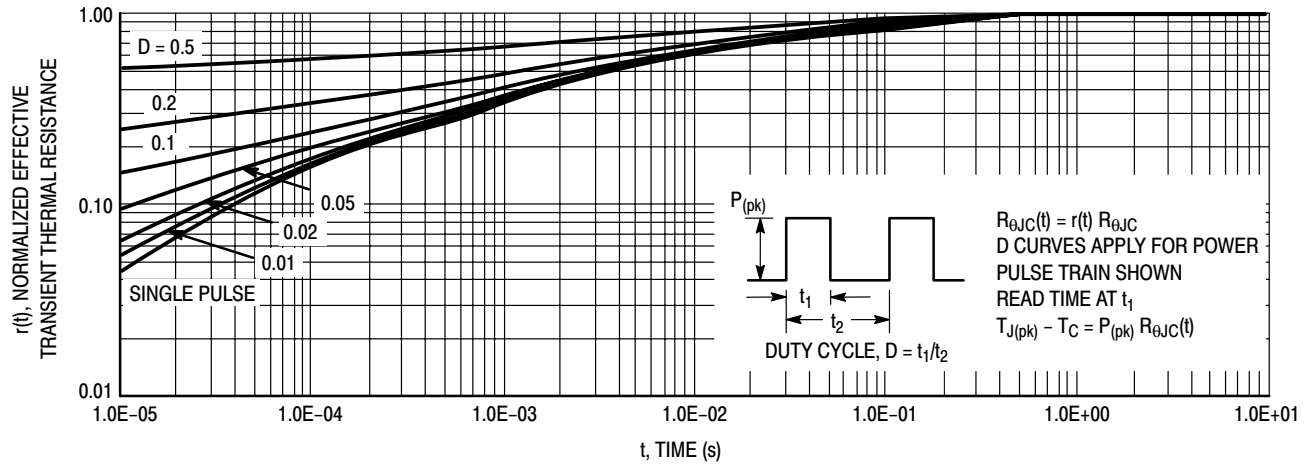


Figure 13. Thermal Response

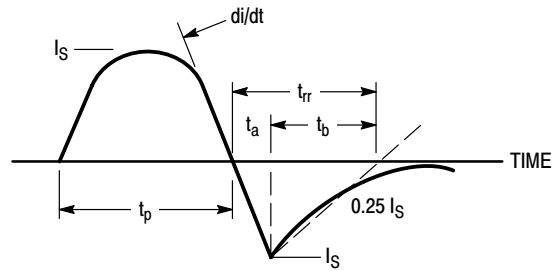
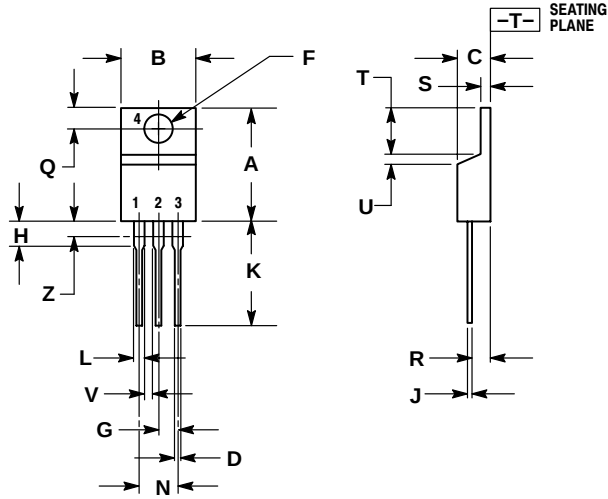


Figure 14. Diode Reverse Recovery Waveform

NTP4302, NTB4302

PACKAGE DIMENSIONS

TO-220 THREE-LEAD
TO-220AB
CASE 221A-09
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

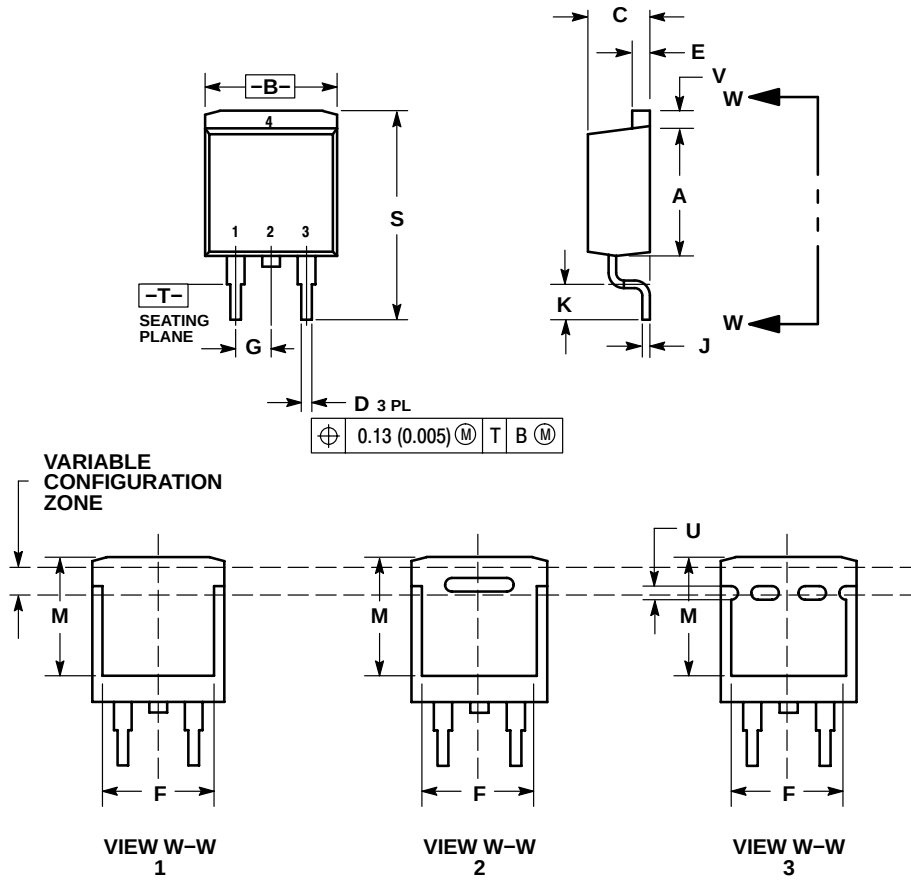
STYLE 5:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NTP4302, NTB4302

PACKAGE DIMENSIONS

D²PAK
CASE 418AA-01
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.036	0.51	0.92
E	0.045	0.055	1.14	1.40
F	0.310	---	7.87	---
G	0.100 BSC		2.54 BSC	
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
M	0.280	---	7.11	---
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 2:

- PIN 1: GATE
2: DRAIN
3: SOURCE
4: DRAIN

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your
local Sales Representative.